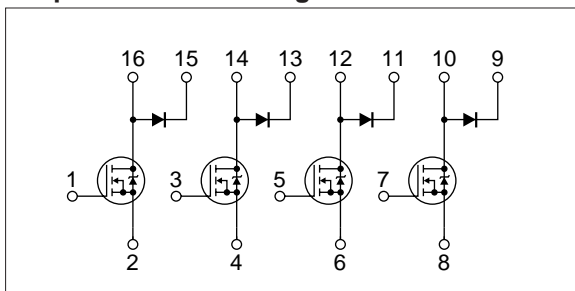


Absolute maximum ratings

(Ta=25°C)

Symbol	Ratings	Unit
V _{DSS}	60	V
V _{GSS}	±10	V
I _D	±2	A
I _{D(pulse)}	±3 (PW≤100μs, Du≤1%)	A
I _F	1.5	A
I _{FSM}	2.5 (PW≤0.5ms, Du≤10%)	A
V _R	120	V
P _T	3 (Ta=25°C, 4-circuit operation)	W
T _{ch}	150	°C
T _{stg}	-40 to +150	°C

Equivalent circuit diagram



Electrical characteristics

(Ta=25°C)

Symbol	Specification			Unit	Conditions
	min	typ	max		
V _{(BR)DSS}	60			V	I _D =250μA, V _{GS} =0V
I _{GSS}			±500	nA	V _{GS} =±10V
I _{DSS}			250	μA	V _{DS} =60V, V _{GS} =0V
V _{TH}	1.0		2.0	V	V _{DS} =10V, I _D =250μA
Re(yfs)	1.2			S	V _{DS} =10V, I _D =1.0A
R _{DS(ON)}		0.19	0.24	Ω	V _{GS} =10V, I _D =1.0A
		0.25	0.30	Ω	V _{GS} =4V, I _D =1.0A
C _{iss}		400		pF	V _{DS} =25V,
C _{oss}		160		pF	f=1.0MHz,
C _{rss}		35		pF	V _{GS} =0V
V _{SD}		1.0	1.5	V	I _{SD} =2A, V _{GS} =0V
t _{rr}		150		ns	I _{SD} =±100mA

Diode for flyback voltage absorption

Symbol	Specification			Unit	Conditions
	min	typ	max		
V _R	120			V	I _R =10μA
V _F			1.6	V	I _F =1A
I _R			100	Ω	V _R =120V
t _{rr}		100		ns	I _F =±100mA

Characteristic curves